

Appl No. 10/605,808
Amdt. dated April 20, 2005
Reply to Office action of March 23, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

- 1 (original): A light emitting device comprising:
- 5 a micro-reflection structure carrier;
 a reflection layer formed over the micro-reflection structure carrier;
 a transparent adhesive layer formed over the reflection layer; and
 a light emitting stack layer formed over the transparent adhesive layer.
- 10 2 (original): The light emitting device of claim 1 further comprising a first reaction layer
 between the reflection layer and the transparent adhesive layer.
- 3 (original): The light emitting device of claim 1 further comprising a second reaction
 layer between the transparent adhesive layer and the light emitting stack layer.
- 15 4 (original): The light emitting device of claim 1 further comprising a first electrode and a
 second electrode formed on the same upper surface of the light emitting stack layer.
- 5 (withdrawn): The light emitting device of claim 1 further comprising a first electrode
20 and a second electrode formed on the upper surface of the light emitting stack layer and
 the lower surface of the micro-reflection structure carrier respectively.
- 6 (original): The light emitting device of claim 1, wherein the light emitting stack layer
 comprises:
- 25 a second reaction layer formed over the transparent adhesive layer;
 a first transparent conductive layer formed over the second reaction layer;
 a first contact layer formed over the transparent conductive layer;
 a first cladding layer formed between the first contact layer and the light emitting

Appl. No. 10/605,808
Amdt. dated April 20, 2005
Reply to Office action of March 23, 2005

- layer;
a second cladding layer formed over the light emitting layer;
a second contact layer formed over the second cladding layer;
a first electrode; and
5 a second electrode formed over the second contact layer.
- 7 (original): The light emitting device of claim 6, wherein the transparent conductive layer has a first surface area and a second surface area, the first contact layer is formed over the first surface area, and the first electrode is formed over the second surface
10 area.
- 8 (original): The light emitting device of claim 7 further comprising a transparent carrier between the second reaction layer and the transparent conductive layer.
- 15 9 (withdrawn): The light emitting device of claim 6, wherein the micro-reflection structure carrier is a conductive micro-reflection structure carrier, the transparent adhesive layer is a transparent conductive adhesive layer, and the first electrode is formed over a lower surface of the conductive micro-reflection structure carrier.
- 20 10 (original): The light emitting device of claim 1, wherein the shape of the micro-reflection structure carrier comprises at least one shape selected from a group consisting of a hemisphere and a pyramid.
- 11 (original): The light emitting device of claim 1, wherein the micro-reflection structure
25 carrier comprises at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, Si, SiC, glass, BN, AlN, and Ge.
- 12 (withdrawn): The light emitting device of claim 9, wherein the conductive

Appl. No. 10/605,808
Amdt. dated April 20, 2005
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micro-reflection structure carrier comprises at least one material selected from a group consisting of Si, GaAs, SiC, GaP, GaAsP, InGaP, AlGaInP, AlGaAs, BN, and AlN.

5 13 (original): The light emitting device of claim 8, wherein the transparent carrier comprises at least one material selected from a group consisting of GaP, SiC, Al₂O₃, and glass.

10 14 (original): The light emitting device of claim 1, wherein the reflection layer comprises at least one material selected from a group consisting of Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn.

15 15 (original): The light emitting device of claim 1, wherein the transparent adhesive layer comprises at least one material selected from a group consisting of polyimide (PI), benzocyclobutane (BCB), and perfluorocyclobutane (PFCB):

16 (original): The light emitting device of claim 2, wherein the first reaction layer comprises at least one material selected from a group consisting of SiNx, Ti, and Cr.

20 17 (original): The light emitting device of claim 3, wherein the second reaction layer comprises at least one material selected from a group consisting of SiNx, Ti, and Cr.

25 18 (original): The light emitting device of claim 6, wherein the second reaction layer comprises at least one material selected from a group consisting of SiNx, Ti, and Cr.

19 (withdrawn): The light emitting device of claim 9, wherein the transparent conductive adhesive layer comprises at least one conductive material selected from a group consisting of intrinsically conducting polymer, and polymer mixed with conducting

Appl. No. 10/605,808
Amdt. dated April 20, 2005
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material.

20 (withdrawn): The light emitting device of claim 19, wherein the conducting material
comprises at least one material selected from a group consisting of indium tin oxide,
5 cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, Au, and Ni/Au.

21 (original): The light emitting device of claim 6, wherein the first cladding layer
comprises at least one material selected from a group consisting of AlGaInP, AlN,
GaN, AlGaN, InGaN, and AlInGaN.
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22 (original): The light emitting device of claim 6, wherein the light emitting layer
comprises at least one material selected from a group consisting of AlGaInP, GaN,
InGaN, and AlInGaN.

15 23 (original): The light emitting device of claim 6, wherein the second cladding layer
comprises at least one material selected from a group consisting of AlGaInP, AlN,
GaN, AlGaN, InGaN, and AlInGaN.

24 (original): The light emitting device of claim 6, wherein the first contact layer
20 comprises at least one material selected from a group consisting of GaP, GaAs, GaAsP,
InGaP, AlGaInP, AlGaAs, GaN, InGaN, and AlGaN.

25 (original): The light emitting device of claim 6, wherein the second contact layer
comprises at least one material selected from a group consisting of GaP, GaAs, GaAsP,
25 InGaP, AlGaInP, AlGaAs, GaN, InGaN, and AlGaN.

26 (original): The light emitting device of claim 6, wherein a second transparent
conductive layer is formed between the second electrode and the second contact layer.

Appl. No. 10/605,808
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27 (original): The light emitting device of claim 6, wherein the first transparent
conductive layer comprises at least one material selected from a group consisting of
indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin
oxide.
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28 (original): The light emitting device of claim 26, wherein the second transparent
conductive layer comprises at least one material selected from a group consisting of
indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin
oxide.
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